

Data sheet acquired from Harris Semiconductor SCHS046A

CMOS Hex Buffer/Converters

The CD4049UB and CD4050B devices are inverting and non-inverting hex buffers, respectively, and feature logic-level conversion using only one supply voltage (V_{CC}). The input-signal high level (V_{IH}) can exceed the V_{CC} supply voltage when these devices are used for logic-level conversions. These devices are intended for use as CMOS to DTL/TTL converters and can drive directly two DTL/TTL loads. (V_{CC} = 5V, V_{OL} \leq 0.4V, and I_{OL} \geq 3.3mA.)

The CD4049UB and CD4050B are designated as replacements for CD4009UB and CD4010B, respectively. Because the CD4049UB and CD4050B require only one power supply, they are preferred over the CD4009UB and CD4010B and should be used in place of the CD4009UB and CD4010B in all inverter, current driver, or logic-level conversion applications. In these applications the CD4049UB and CD4050B are pin compatible with the CD4009UB and CD4010B respectively, and can be substituted for these devices in existing as well as in new designs. Terminal No. 16 is not connected internally on the CD4049UB or CD4050B, therefore, connection to this terminal is of no consequence to circuit operation. For applications not requiring high sink-current or voltage conversion, the CD4069UB Hex Inverter is recommended.

Features

- · CD4049UB Inverting
- CD4050B Non-Inverting
- · High Sink Current for Driving 2 TTL Loads
- High-To-Low Level Logic Conversion
- 100% Tested for Quiescent Current at 20V
- Maximum Input Current of 1µA at 18V Over Full Package Temperature Range; 100nA at 18V and 25°C
- 5V, 10V and 15V Parametric Ratings

Applications

- CMOS to DTL/TTL Hex Converter
- · CMOS Current "Sink" or "Source" Driver
- CMOS High-To-Low Logic Level Converter

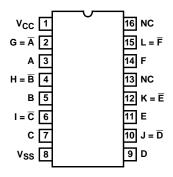
Ordering Information

PART NUMBER	TEMP. RANGE (°C)	PACKAGE	PKG. NO.
CD4049UBE	-55 to 125	16 Ld PDIP	E16.3
CD4050BE	-55 to 125	16 Ld PDIP	E16.3
CD4049UBF	-55 to 125	16 Ld CERDIP	F16.3
CD4050BF	-55 to 125	16 Ld CERDIP	F16.3
CD4050BM	-55 to 125	16 Ld SOIC	M16.3

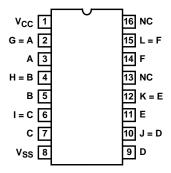
NOTE: Wafer and die for this part number is available which meets all electrical specifications. Please contact your local sales office or customer service for ordering information.

Pinouts

CD4049UB (PDIP, CERDIP) TOP VIEW



CD4050B (PDIP, CERDIP, SOIC) TOP VIEW



Functional Block Diagrams

CD4049UB

A
$$\frac{3}{}$$
 $\frac{2}{}$ $G = \overline{A}$

B $\frac{5}{}$ $\frac{4}{}$ $H = \overline{B}$

C $\frac{7}{}$ $\frac{6}{}$ $I = \overline{C}$

D $\frac{9}{}$ $\frac{10}{}$ $J = \overline{D}$

E $\frac{11}{}$ $\frac{12}{}$ $K = \overline{E}$

V_{CC} $\frac{1}{}$ $\frac{15}{}$ $L = \overline{F}$

V_{CC} $\frac{8}{}$ $NC = 13$
 $NC = 16$

CD4050B

A
$$\frac{3}{0}$$
 $\frac{2}{0}$ G = A

B $\frac{5}{0}$ $\frac{4}{0}$ H = B

C $\frac{7}{0}$ $\frac{6}{0}$ I = C

D $\frac{9}{0}$ $\frac{10}{0}$ J = D

E $\frac{11}{0}$ $\frac{12}{0}$ K = E

F $\frac{14}{0}$ $\frac{15}{0}$ L = F

V_{CC} $\frac{8}{0}$ NC = 13

NC = 16

Schematic Diagrams

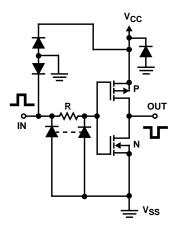


FIGURE 1A. SCHEMATIC DIAGRAM OF CD4049UB, 1 OF 6 IDENTICAL UNITS

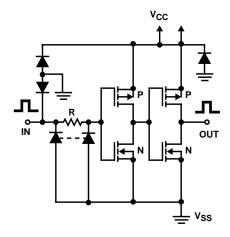


FIGURE 1B. SCHEMATIC DIAGRAM OF CD4050B, 1 OF 6 IDENTICAL UNITS

CD4049UB, CD4050B

Absolute Maximum Ratings

Operating Conditions

Temperature Range -55°C to 125°C

Thermal Information

Thermal Resistance (Typical, Note 1)	θ_{JA} (oC/W)	θ_{JC} (oC/W)
PDIP Package	90	N/A
CERDIP Package	130	55
SOIC Package	100	N/A
Maximum Junction Temperature (Plastic F	ackage)	150 ⁰ C
Maximum Storage Temperature Range	6	5°C to 150°C
Maximum Lead Temperature (Soldering 1	0s)	265 ⁰ C
(SOIC - Lead Tips Only)		

CAUTION: Stresses above those listed in "Absolute Maximum Ratings" may cause permanent damage to the device. This is a stress only rating and operation of the device at these or any other conditions above those indicated in the operational sections of this specification is not implied.

NOTE

1. $\theta_{\mbox{\scriptsize JA}}$ is measured with the component mounted on an evaluation PC board in free air.

DC Electrical Specifications

				L	IMITS A	T INDICA	ATED TE	MPERAT	URE (°C	C)	
	TES	T CONDIT	IONS					25			
PARAMETER	V _O (V)	V _{IN} (V)	V _{CC} (V)	-55	-40	85	125	MIN	TYP	MAX	UNITS
Quiescent Device Current	-	0,5	5	1	1	30	30	-	0.02	1	μΑ
I _{DD} (Max)	-	0,10	10	2	2	60	60	-	0.02	2	μΑ
	-	0,15	15	4	4	120	120	-	0.02	4	μΑ
	-	0,20	20	20	20	600	600	-	0.04	20	μΑ
Output Low (Sink) Current	0.4	0,5	4.5	3.3	3.1	2.1	1.8	2.6	5.2	-	mA
I _{OL} (Min)	0.4	0,5	5	4	3.8	2.9	2.4	3.2	6.4	-	mA
	0.5	0,10	10	10	9.6	6.6	5.6	8	16	-	mA
	1.5	0,15	15	26	25	20	18	24	48	-	mA
Output High (Source) Current I _{OH} (Min)	4.6	0,5	5	-0.81	-0.73	-0.58	-0.48	-0.65	-1.2	-	mA
	2.5	0,5	5	-2.6	-2.4	-1.9	-1.55	-2.1	-3.9	-	mA
	9.5	0,10	10	-2.0	-1.8	-1.35	-1.18	-1.65	-3.0	-	mA
	13.5	0,15	15	-5.2	-4.8	-3.5	-3.1	-4.3	-8.0	-	mA
Out Voltage Low Level	-	0,5	5	0.05	0.05	0.05	0.05	-	0	0.05	V
V _{OL} (Max)	-	0,10	10	0.05	0.05	0.05	0.05	-	0	0.05	V
	-	0,15	5	0.05	0.05	0.05	0.05	-	0	0.05	V
Output Voltage High Level	-	0,5	5	4.95	4.95	4.95	4.95	4.95	5	-	V
V _{OH} (Min)	-	0,10	10	9.95	9.95	9.95	9.95	9.95	10	-	V
	-	0,15	15	14.95	14.95	14.95	14.95	14.95	15	-	V
Input Low Voltage, V _{IL} (Max)	4.5	-	5	1	1	1	1	-	-	1	V
CD4049UB	9	-	10	2	2	2	2	-	-	2	V
	13.5	-	15	2.5	2.5	2.5	2.5	-	-	2.5	V
Input Low Voltage, V _{IL} (Max) CD4050B	0.5	-	5	1.5	1.5	1.5	1.5	-	-	1.5	V
	1	-	10	3	3	3	3	-	-	3	V
	1.5	-	15	4	4	4	4	-	-	4	V
Input High Voltage, V _{IH} Min	0.5	-	5	4	4	4	4	4	-	-	V
CD4049UB	1	-	10	8	8	8	8	8	-	-	V
	1.5	-	15	12.5	12.5	12.5	12.5	12.5	-	-	V

CD4049UB, CD4050B

DC Electrical Specifications (Continued)

				LIMITS AT INDICATED TEMPERATURE (°C)							
	TEST CONDITIONS						25				
PARAMETER	V _O (V)	V _{IN} (V)	V _{CC} (V)	-55	-40	85	125	MIN	TYP	MAX	UNITS
Input High Voltage, V _{IH} Min	4.5	-	5	3.5	3.5	3.5	3.5	3.5	-	-	V
CD4050B	9	-	10	7	7	7	7	7	-	-	V
	13.5	-	15	11	11	11	11	11	-	-	V
Input Current, I _{IN} Max	-	0,18	18	±0.1	±0.1	±1	±1	-	±10 ⁻⁵	±0.1	μΑ

$\textbf{AC Electrical Specifications} \qquad \text{T}_{A} = 25^{0}\text{C}, \text{ Input } t_{r}, \ t_{f} = 20\text{ns}, \ C_{L} = 50\text{pF}, \ R_{L} = 200\text{k}\Omega$

	TEST CO	NDITIONS	LIMITS (ALL	LIMITS (ALL PACKAGES)		
PARAMETER	V _{IN}	v _{cc}	TYP	MAX	UNITS	
Propagation Delay Time	5	5	60	120	ns	
Low to High, t _{PLH} CD4049UB	10	10	32	65	ns	
	10	5	45	90	ns	
	15	15	25	50	ns	
	15	5	45	90	ns	
Propagation Delay Time	5	5	70	140	ns	
Low to High, t _{PLH} CD4050B	10	10	40	80	ns	
	10	5	45	90	ns	
	15	15	30	60	ns	
	15	5	40	80	ns	
Propagation Delay Time High to Low, t _{PHL} CD4049UB	5	5	32	65	ns	
	10	10	20	40	ns	
	10	5	15	30	ns	
	15	15	15	30	ns	
	15	5	10	20	ns	
Propagation Delay Time	5	5	55	110	ns	
High to Low, t _{PHL} CD4050B	10	10	22	55	ns	
	10	5	50	100	ns	
	15	15	15	30	ns	
	15	5	50	100	ns	
Transition Time, Low to High, t _{TLH}	5	5	80	160	ns	
	10	10	40	80	ns	
	15	15	30	60	ns	
Transition Time, High to Low, t _{THL}	5	5	30	60	ns	
	10	10	20	40	ns	
	15	15	15	30	ns	
nput Capacitance, C _{IN} CD4049UB	-	-	15	22.5	pF	
nput Capacitance, C _{IN} CD4050B	-	-	5	7.5	pF	

Typical Performance Curves

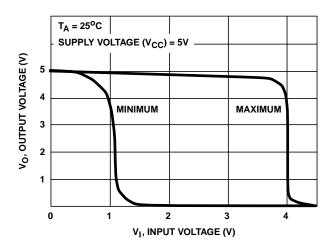


FIGURE 2. MINIMUM AND MAXIMUM VOLTAGE TRANSFER CHARACTERISTICS FOR CD4049UB

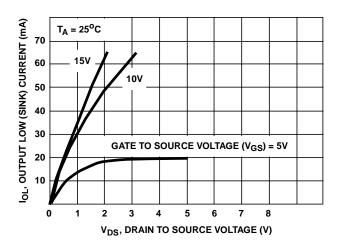


FIGURE 4. TYPICAL OUTPUT LOW (SINK) CURRENT CHARACTERISTICS

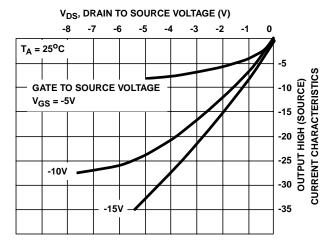


FIGURE 6. TYPICAL OUTPUT HIGH (SOURCE) CURRENT CHARACTERISTICS

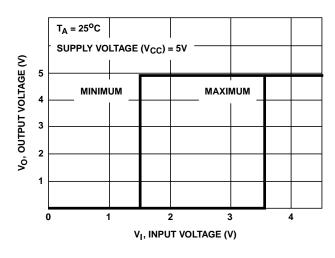


FIGURE 3. MINIMUM AND MAXIMUM VOLTAGE TRANSFER CHARACTERISTICS FOR CD4050B

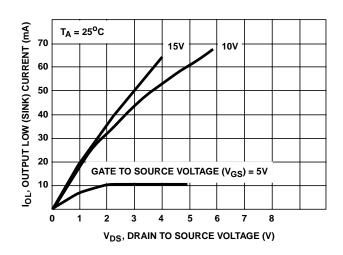


FIGURE 5. MINIMUM OUTPUT LOW (SINK) CURRENT DRAIN CHARACTERISTICS

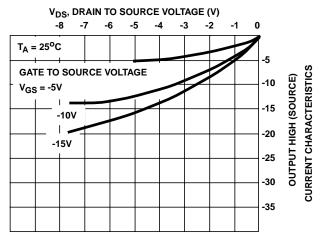


FIGURE 7. MINIMUM OUTPUT HIGH (SOURCE) CURRENT CHARACTERISTICS

Typical Performance Curves (Continued)

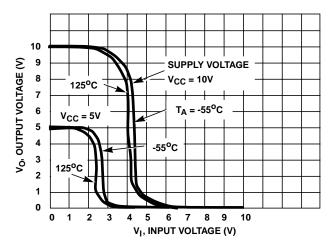


FIGURE 8. TYPICAL VOLTAGE TRANSFER CHARACTERISTICS
AS A FUNCTION OF TEMPERATURE FOR CD4049UB

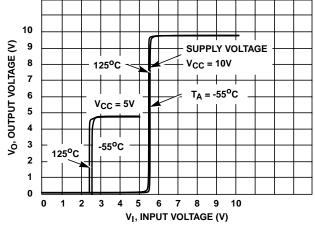


FIGURE 9. TYPICAL VOLTAGE TRANSFER CHARACTERISTICS
AS A FUNCTION OF TEMPERATURE FOR CD4050B

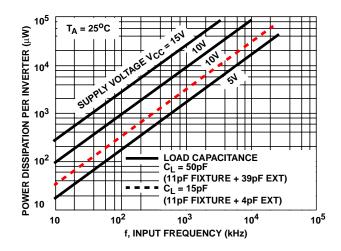


FIGURE 10. TYPICAL POWER DISSIPATION vs FREQUENCY CHARACTERISTICS

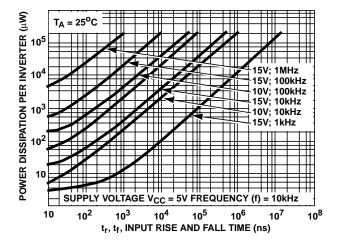


FIGURE 11. TYPICAL POWER DISSIPATION VS INPUT RISE AND FALL TIMES PER INVERTER FOR CD4049UB

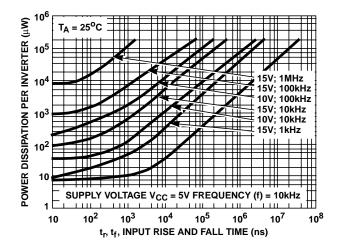


FIGURE 12. TYPICAL POWER DISSIPATION VS INPUT RISE AND FALL TIMES PER INVERTER FOR CD4050B

Test Circuits

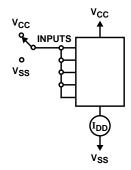
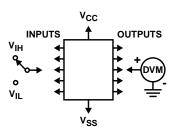
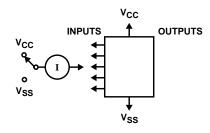


FIGURE 13. QUIESCENT DEVICE CURRENT TEST CIRCUIT



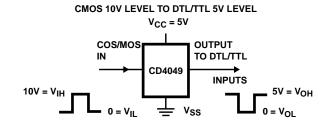
NOTE: Test any one input with other inputs at $\rm V_{CC}$ or $\rm V_{SS}$

FIGURE 14. INPUT VOLTAGE TEST CIRCUIT



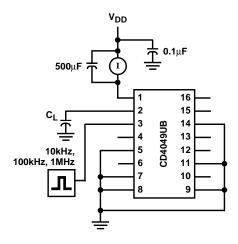
NOTE: Measure inputs sequentially, to both $\rm V_{CC}$ and $\rm V_{SS}$ connect all unused inputs to either $\rm V_{CC}$ or $\rm V_{SS}.$

FIGURE 15. INPUT CURRENT TEST CIRCUIT



In Terminal - 3, 5, 7, 9, 11, or 14 Out Terminal - 2, 4, 6, 10, 12 or 15 V_{CC} Terminal - 1 V_{SS} Terminal - 8

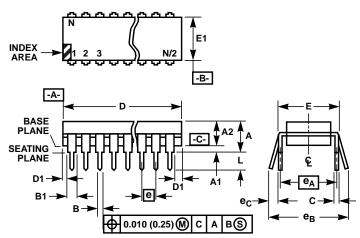
FIGURE 16. LOGIC LEVEL CONVERSION APPLICATION



CL INCLUDES FIXTURE CAPACITANCE

FIGURE 17. DYNAMIC POWER DISSIPATION TEST CIRCUITS

Dual-In-Line Plastic Packages (PDIP)



NOTES:

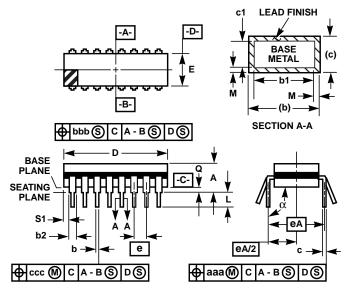
- Controlling Dimensions: INCH. In case of conflict between English and Metric dimensions, the inch dimensions control.
- 2. Dimensioning and tolerancing per ANSI Y14.5M-1982.
- Symbols are defined in the "MO Series Symbol List" in Section 2.2 of Publication No. 95.
- Dimensions A, A1 and L are measured with the package seated in JE-DEC seating plane gauge GS-3.
- D, D1, and E1 dimensions do not include mold flash or protrusions. Mold flash or protrusions shall not exceed 0.010 inch (0.25mm).
- E and e_A are measured with the leads constrained to be perpendicular to datum -C-.
- 7. e_B and e_C are measured at the lead tips with the leads unconstrained. e_C must be zero or greater.
- 8. B1 maximum dimensions do not include dambar protrusions. Dambar protrusions shall not exceed 0.010 inch (0.25mm).
- 9. N is the maximum number of terminal positions.
- Corner leads (1, N, N/2 and N/2 + 1) for E8.3, E16.3, E18.3, E28.3, E42.6 will have a B1 dimension of 0.030 - 0.045 inch (0.76 - 1.14mm).

E16.3 (JEDEC MS-001-BB ISSUE D)
16 LEAD DUAL-IN-LINE PLASTIC PACKAGE

	INC	HES	MILLIM		
SYMBOL	MIN	MIN MAX MIN		MAX	NOTES
А	-	0.210	-	5.33	4
A1	0.015	-	0.39	-	4
A2	0.115	0.195	2.93	4.95	-
В	0.014	0.022	0.356	0.558	-
B1	0.045	0.070	1.15	1.77	8, 10
С	0.008	0.014	0.204	0.355	-
D	0.735	0.775	18.66	19.68	5
D1	0.005	-	0.13	-	5
Е	0.300	0.325	7.62	8.25	6
E1	0.240	0.280	6.10	7.11	5
е	0.100	BSC	2.54 BSC		-
e _A	0.300	BSC	7.62	BSC	6
e _B	-	0.430	-	10.92	7
L	0.115	0.150	2.93	3.81	4
N	16		1	6	9

Rev. 0 12/93

Ceramic Dual-In-Line Frit Seal Packages (CERDIP)



NOTES:

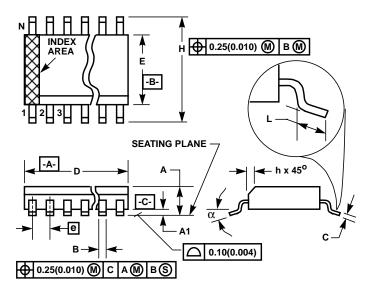
- Index area: A notch or a pin one identification mark shall be located adjacent to pin one and shall be located within the shaded area shown. The manufacturer's identification shall not be used as a pin one identification mark.
- The maximum limits of lead dimensions b and c or M shall be measured at the centroid of the finished lead surfaces, when solder dip or tin plate lead finish is applied.
- Dimensions b1 and c1 apply to lead base metal only. Dimension M applies to lead plating and finish thickness.
- Corner leads (1, N, N/2, and N/2+1) may be configured with a partial lead paddle. For this configuration dimension b3 replaces dimension b2.
- This dimension allows for off-center lid, meniscus, and glass overrun.
- 6. Dimension Q shall be measured from the seating plane to the base plane.
- 7. Measure dimension S1 at all four corners.
- 8. N is the maximum number of terminal positions.
- 9. Dimensioning and tolerancing per ANSI Y14.5M 1982.
- 10. Controlling dimension: INCH.

F16.3 MIL-STD-1835 GDIP1-T16 (D-2, CONFIGURATION A) 16 LEAD CERAMIC DUAL-IN-LINE FRIT SEAL PACKAGE

	INC	HES	MILLIM	ETERS		
SYMBOL	MIN	MAX	MIN	MAX	NOTES	
А	-	0.200	-	5.08	-	
b	0.014	0.026	0.36	0.66	2	
b1	0.014	0.023	0.36	0.58	3	
b2	0.045	0.065	1.14	1.65	-	
b3	0.023	0.045	0.58	1.14	4	
С	0.008	0.018	0.20	0.46	2	
c1	0.008	0.015	0.20	0.38	3	
D	-	0.840	-	21.34	5	
Е	0.220	0.310	5.59	7.87	5	
е	0.100	BSC	2.54	-		
eA	0.300	0.300 BSC		7.62 BSC		
eA/2	0.150	BSC	3.81	-		
L	0.125	0.200	3.18	5.08	-	
Q	0.015	0.060	0.38	1.52	6	
S1	0.005	-	0.13	-	7	
α	90°	105 ⁰	90°	105 ⁰	-	
aaa	-	0.015	-	0.38	-	
bbb	-	0.030	-	0.76	-	
ccc	-	0.010	-	0.25	-	
М	-	0.0015	-	0.038	2, 3	
N	1	6	1	6	8	

Rev. 0 4/94

Small Outline Plastic Packages (SOIC)



NOTES:

- Symbols are defined in the "MO Series Symbol List" in Section 2.2 of Publication Number 95.
- 2. Dimensioning and tolerancing per ANSI Y14.5M-1982.
- Dimension "D" does not include mold flash, protrusions or gate burrs.
 Mold flash, protrusion and gate burrs shall not exceed 0.15mm (0.006 inch) per side.
- Dimension "E" does not include interlead flash or protrusions. Interlead flash and protrusions shall not exceed 0.25mm (0.010 inch) per side.
- 5. The chamfer on the body is optional. If it is not present, a visual index feature must be located within the crosshatched area.
- 6. "L" is the length of terminal for soldering to a substrate.
- 7. "N" is the number of terminal positions.
- 8. Terminal numbers are shown for reference only.
- The lead width "B", as measured 0.36mm (0.014 inch) or greater above the seating plane, shall not exceed a maximum value of 0.61mm (0.024 inch)
- 10. Controlling dimension: MILLIMETER. Converted inch dimensions are not necessarily exact.

M16.3 (JEDEC MS-013-AA ISSUE C)
16 LEAD WIDE BODY SMALL OUTLINE PLASTIC PACKAGE

	INC	HES	MILLIN		
SYMBOL	MIN	MAX	MIN	MAX	NOTES
Α	0.0926	0.1043	2.35	2.65	-
A1	0.0040	0.0118	0.10	0.30	-
В	0.013	0.0200	0.33	0.51	9
С	0.0091	0.0125	0.23	0.32	-
D	0.3977	0.4133	10.10	10.50	3
Е	0.2914	0.2992	7.40	7.60	4
е	0.050	BSC	1.27 BSC		-
Н	0.394	0.419	10.00	10.65	-
h	0.010	0.029	0.25	0.75	5
L	0.016	0.050	0.40	1.27	6
N	16		16		7
α	0°	8 ⁰	0°	8 ⁰	-

Rev. 0 12/93

IMPORTANT NOTICE

Texas Instruments and its subsidiaries (TI) reserve the right to make changes to their products or to discontinue any product or service without notice, and advise customers to obtain the latest version of relevant information to verify, before placing orders, that information being relied on is current and complete. All products are sold subject to the terms and conditions of sale supplied at the time of order acknowledgement, including those pertaining to warranty, patent infringement, and limitation of liability.

TI warrants performance of its semiconductor products to the specifications applicable at the time of sale in accordance with TI's standard warranty. Testing and other quality control techniques are utilized to the extent TI deems necessary to support this warranty. Specific testing of all parameters of each device is not necessarily performed, except those mandated by government requirements.

CERTAIN APPLICATIONS USING SEMICONDUCTOR PRODUCTS MAY INVOLVE POTENTIAL RISKS OF DEATH, PERSONAL INJURY, OR SEVERE PROPERTY OR ENVIRONMENTAL DAMAGE ("CRITICAL APPLICATIONS"). TI SEMICONDUCTOR PRODUCTS ARE NOT DESIGNED, AUTHORIZED, OR WARRANTED TO BE SUITABLE FOR USE IN LIFE-SUPPORT DEVICES OR SYSTEMS OR OTHER CRITICAL APPLICATIONS. INCLUSION OF TI PRODUCTS IN SUCH APPLICATIONS IS UNDERSTOOD TO BE FULLY AT THE CUSTOMER'S RISK.

In order to minimize risks associated with the customer's applications, adequate design and operating safeguards must be provided by the customer to minimize inherent or procedural hazards.

TI assumes no liability for applications assistance or customer product design. TI does not warrant or represent that any license, either express or implied, is granted under any patent right, copyright, mask work right, or other intellectual property right of TI covering or relating to any combination, machine, or process in which such semiconductor products or services might be or are used. TI's publication of information regarding any third party's products or services does not constitute TI's approval, warranty or endorsement thereof.

Copyright © 1999, Texas Instruments Incorporated